Philips Semiconductors

Product specification

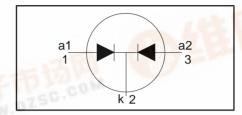
Rectifier diodes Schottky barrier

PBYR2545CT, PBYR2545CTB series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{O(AV)} = 30 \text{ A}$
 $V_F \le 0.62 \text{ V}$

GENERAL DESCRIPTION

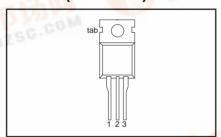
Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR2545CT series is supplied in the SOT78 conventional leaded package. The PBYR2545CTB series is supplied in the SOT404 surface mounting package.

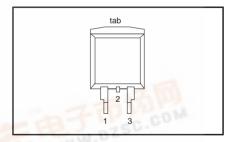
PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k) 1		
3	anode 2 (a)		
tab	cathode (k)		

SOT78 (TO220AB)



SOT404



LIMITING VALUES

f.dzsc.com

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS		RAMETER CONDITIONS MIN. N		MA	Χ.	UNIT
	WWW.D		BYR25 BYR25		40CT 40CTB	45CT 45CTB		
V_{RRM}	Peak repetitive reverse voltage			-	40	45	V	
V_{RWM}	Working peak reverse voltage			-	40	45	V	
V_{R}	Continuous reverse voltage	T _{mb} ≤ 113 °C		-	40	45	V	
$I_{O(AV)}$	Average rectified forward current (both diodes conducting) ²	square wave; $\delta = 0.5$; $T_{mb} \le 126 ^{\circ}C$		Ė	30		A	
I _{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 126 ^{\circ}C$		-	30		Α	
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; T_j = 125 °C prio surge; with reapplied $V_{RRM(j)}$	or to	-	18 20		A A	
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition i limited by T _{i max}	rate	-	1		Α	
T_j	Operating junction temperature	initiaco by I _{jmax}		-	15	0	°C	
T_{stg}	Storage temperature			- 65	17	5	°C	

1. It is not possible to make connection to pin 2 of the SOT404 package.
2. SOT78 package. For output currents greater than 20A the cathode connection should be made to the metal prounting tab.

PBYR2545CT, PBYR2545CTB series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-a}	to mounting base	per diode both diodes SOT78 package in free air SOT404 package, pcb mounted, minimum footprint, FR4 board	1111	- - 60 50	1.5 1 - -	K/W K/W K/W K/W

ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified

1	•					
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage per diode	$I_F = 20 \text{ A}; T_i = 125^{\circ}\text{C}$ $I_F = 30 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.58	0.62	V
		$ I_F = 30 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.72	0.76	V
		$I_{\rm F} = 30 {\rm A}$	-	0.72	0.82	V
I _R	Reverse current per diode	$V_R = V_{RWM}$	-	0.3	2	mΑ
		$V_R = V_{RWM}$; $T_i = 100$ °C	-	30	40	mA
C _d	Junction capacitance per diode	$V_R = V_{RWM}^{NWW}$; $T_j = 100^{\circ}C$ $V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_j = 25^{\circ}C$ to 125°C	-	530	-	pF

PBYR2545CT, PBYR2545CTB series

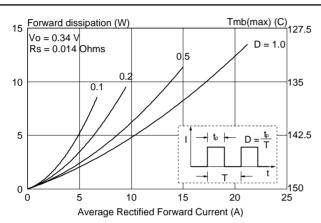
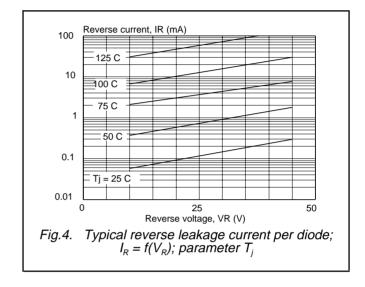


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.



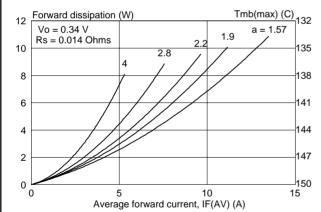


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

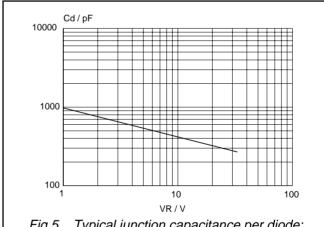


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

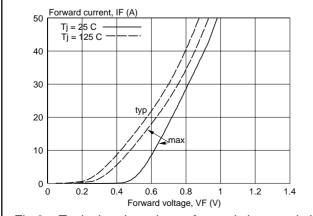


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

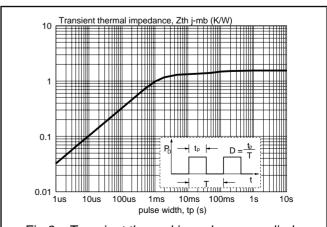
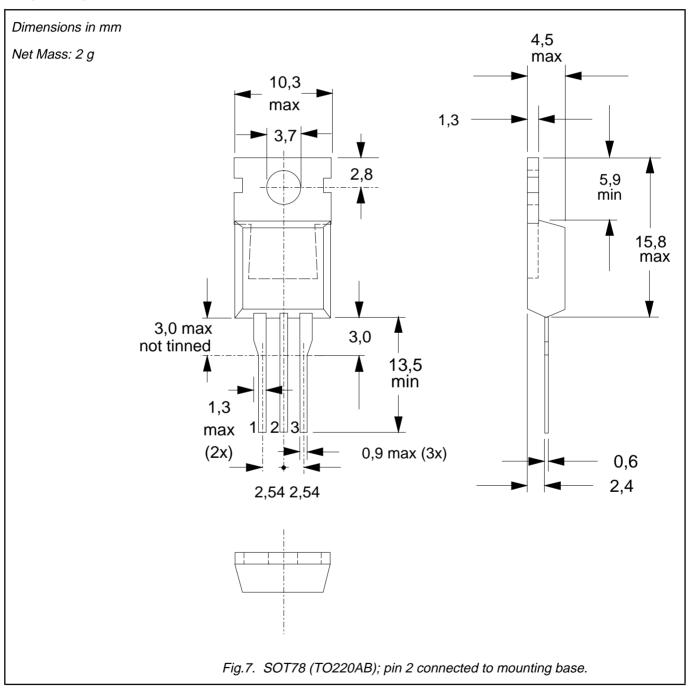


Fig.6. Transient thermal impedance per diode; $Z_{th i-mb} = f(t_p)$.

PBYR2545CT, PBYR2545CTB series

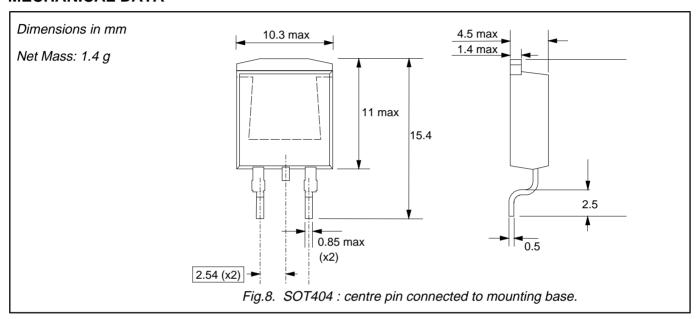
MECHANICAL DATA



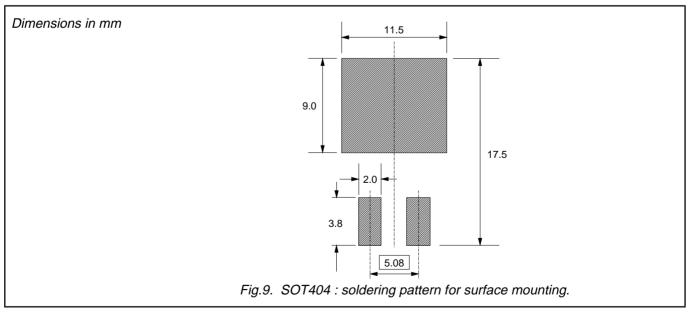
- Refer to mounting instructions for SOT78 (TO220) envelopes.
 Epoxy meets UL94 V0 at 1/8".

PBYR2545CT, PBYR2545CTB series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes
1. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<u> </u>	

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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